# XP06435 (XP6435)

## Silicon PNP epitaxial planar type

For high-frequency amplification

#### Features

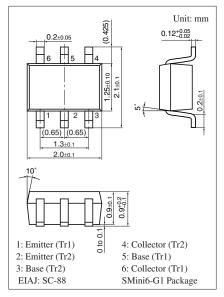
- Two elements incorporated into one package
- Reduction of the mounting area and assembly cost by one half

#### Basic Part Number

• 2SA1022  $\times$  2

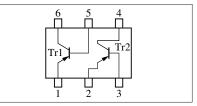
### Absolute Maximum Ratings $T_a = 25^{\circ}C$

•				
Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	-30	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	-20	V	
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	-5	V	
Collector current	I <sub>C</sub>	-30	mA	
Total power dissipation	PT	150	mW	
Junction temperature	Tj	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	



#### Marking Symbol: 7W

#### Internal Connection

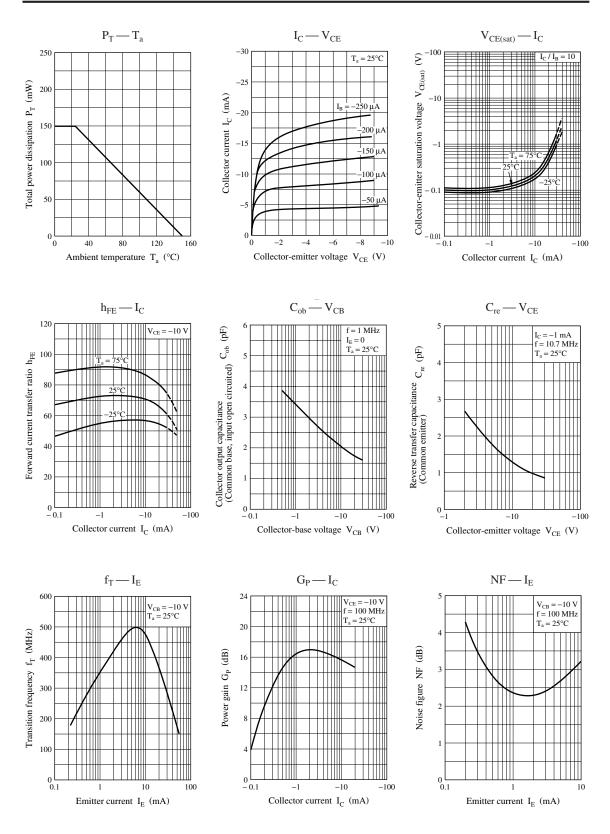


Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Base-emitter voltage	V <sub>BE</sub>	$V_{CE} = -10 \text{ V}, I_C = -1 \text{ mA}$		- 0.7		V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = -10 \text{ V}, I_E = 0$			- 0.1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = -20 \text{ V}, I_B = 0$			-100	μΑ
Emitter-base cutoff current (Collector open)	I <sub>EBO</sub>	$V_{EB} = -5 V, I_C = 0$			-10	μΑ
Forward current transfer ratio	h <sub>FE</sub>	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}$	50		220	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = -1 \text{ mA}$		- 0.1		V
Transition frequency	f <sub>T</sub>	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 200 \text{ MHz}$	150			MHz
Noise figure	NF	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 5 \text{ MHz}$		2.8		dB
Reverse transfer impedance	Z <sub>rb</sub>	$V_{CB} = -10 \text{ V}, I_E = 1 \text{ mA}, f = 2 \text{ MHz}$		22		Ω
Reverse transfer capacitance (Common emitter)	C <sub>re</sub>	$V_{CE} = -10 \text{ V}, I_C = -1 \text{ mA}, f = 10.7 \text{ MHz}$		1.2		pF

### Electrical Characteristics $T_a = 25^{\circ}C \pm 2^{\circ}C$

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

Note) The part number in the parenthesis shows conventional part number.



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